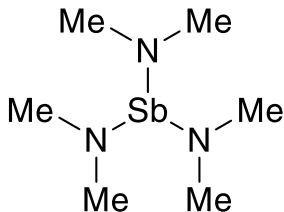


Catalog # 51-5000 Tris(dimethylamino)antimony (99.99%-Sb) PURATREM



Thermal Behavior:

- Boiling point: 32-34°C/0.45Torr [1]; 50-52°C/0.5 Torr; 60°C/10⁻¹ Torr [97]
- Decomposition: >300°C [2]
- Melting point 10°C [8]

Technical Notes:

1. ALD/CVD precursor for antimony containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Sb ₂ O ₅	ALD	-	-	O ₃	120°C	3
Sb ₂ S ₃	ALD	40°C	-	H ₂ S	120°C	4-5
Sb ₂ Se ₃	ALD	RT	-	SDMDTC	150°C	6
Ti _x Sb _y Te _z	PE-ALD	-	-	^{PL} H ₂ , TiCl ₄ , Te(C ₄ H ₉) ₂	230°C	7
GeSbTe	PE-ALD	RT	- 3-6.75 Torr	Ge(NMe ₂) ₄ , ^{PL} H ₂ , Te(ⁱ Pr) ₂ or Te ₂ (n- C ₄ H ₉) ₂	200-350°C 100°C	8-9
CuSbS ₂	ALD	55°C	-	H ₂ S, CuAMD	100-155°C	10
Se:Sb _x Te _y	ALD	35°C	3 Torr	Te(^t Bu) ₂ , Se(SiMe ₃) ₂	80-300°C	11

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